



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
85V	98mΩ@10V	3.5A
	116mΩ@4.5V	

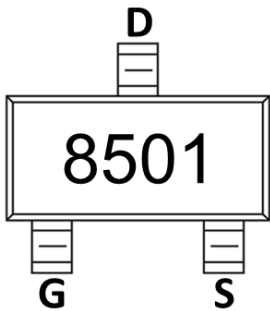
Feature

- Surface Mount Package
- High Density Cell Design for Extremely Low RDS(ON)
- Voltage Controlled Small Signal Switch
- Rugged and Reliable

Application

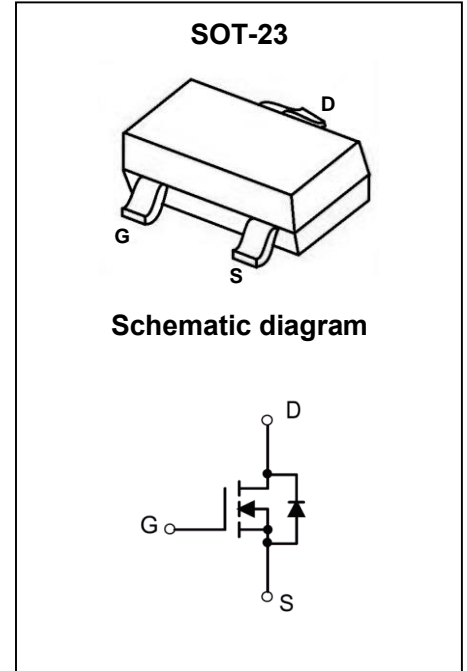
- Small Servo Motor Controls
- Power MOSFET Gate Drivers
- Switching Application

MARKING:



ABSOLUTE MAXIMUM RATINGS (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	85	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current ^{1,2}	I_D	3.5	A
Pulsed Drain Current (tp=10μs)	I_{DM}	14	A
Power Dissipation	P_D	1.25	W
Thermal Resistance from Junction to Ambient ^{1,2}	$R_{θJA}$	100	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~ +150	°C



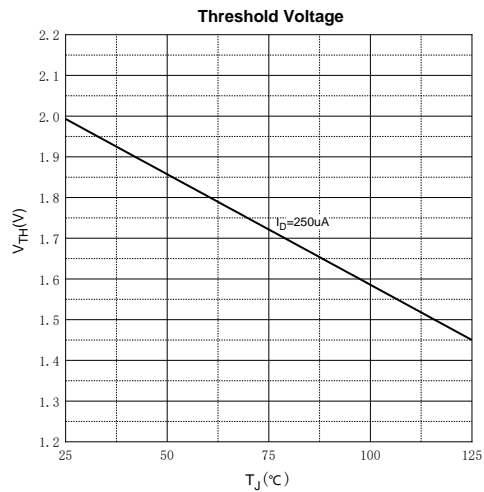
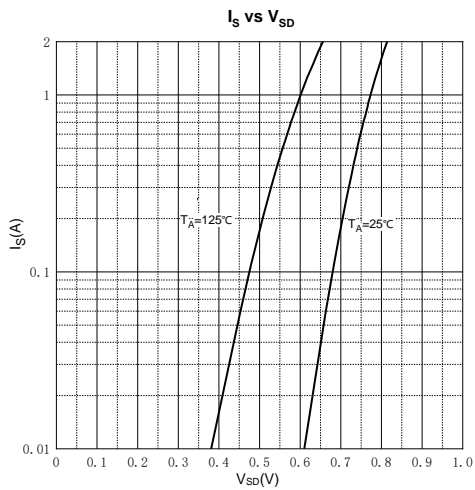
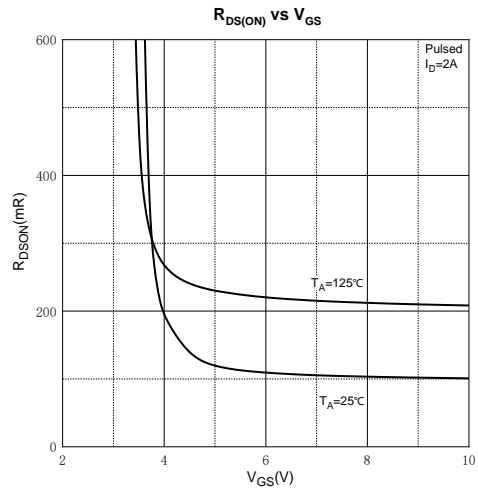
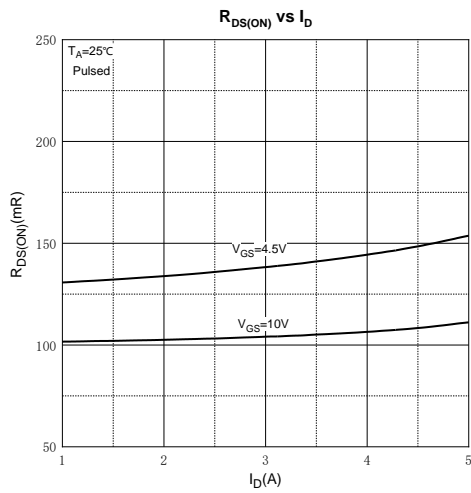
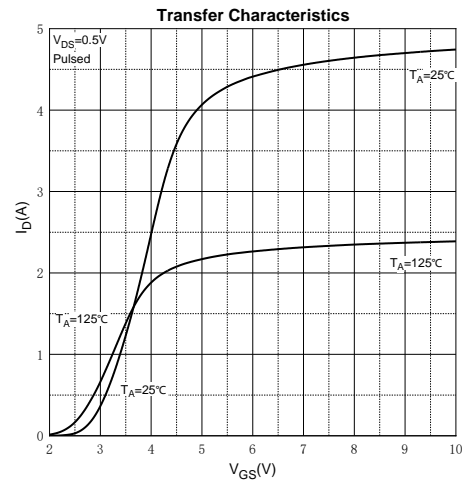
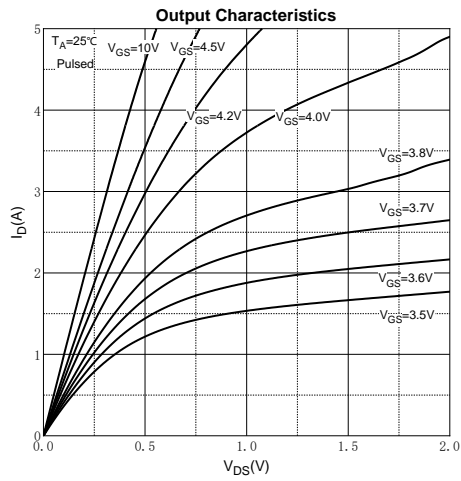
MOSFET ELECTRICAL CHARACTERISTICS($T_a = 25^\circ\text{C}$ unless otherwise noted)

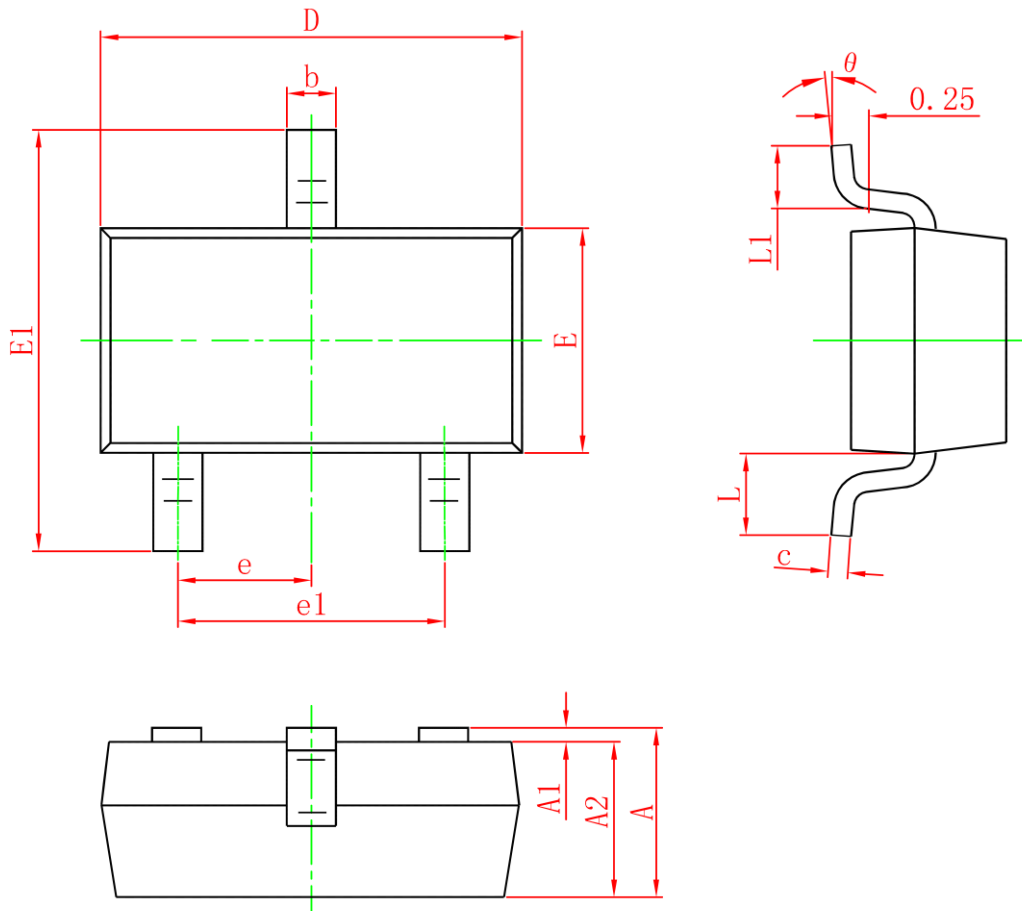
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	85			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 85V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics³						
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	2	3	V
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 2A$		98	150	m Ω
		$V_{GS} = 4.5V, I_D = 2A$		116	180	
Forward transconductance	g_{FS}	$V_{DS} = 5V, I_D = 3A$		5		S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 42.5V, V_{GS} = 0V, f = 1MHz$		335		pF
Output Capacitance	C_{oss}			21.5		
Reverse Transfer Capacitance	C_{rss}			17.3		
Switching Characteristics						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 10V, V_{DD} = 50V, R_L = 19\Omega,$ $R_G = 3\Omega$		6		ns
Turn-on rise time	t_r			4		
Turn-off delay time	$t_{d(off)}$			20		
Turn-off fall time	t_f			4		
Total Gate Charge	Q_g	$V_{DS} = 43V, I_D = 2A, V_{GS} = 10V$		9.8		nC
Gate-Source Charge	Q_{gs}			1.62		
Gate-Drain Charge	Q_{gd}			3.15		
Diode Characteristics						
Diode forward voltage ³	V_{SD}	$I_S = 2A, V_{GS} = 0V$			1.2	V

Notes :

- $R_{\theta JA}$ is measured with the device mounted on 1 in² FR4 board with 1oz. single side copper, in a still air environment with $T_a = 25^\circ\text{C}$.
- $R_{\theta JA}$ is measured in the steady state
- Pulse test : Pulse width $\leq 380\mu s$, duty cycle $\leq 2\%$.

Typical Characteristics



SOT-23 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0	0.100	0	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.150	1.500	0.045	0.059
E1	2.250	2.650	0.089	0.104
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°